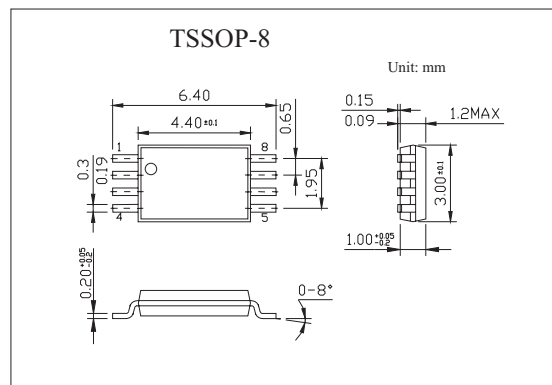
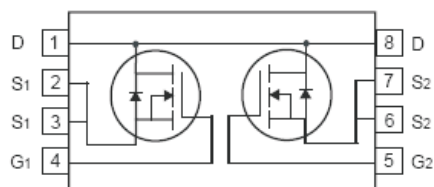


Dual N-Channel Enhancement Mode Field Effect Transistor

■ Features

- 5A,20V. $r_{DS(on)} = 0.025 \Omega @ V_{GS} = 4.5 V$
 $r_{DS(on)} = 0.040 \Omega @ V_{GS} = 2.5 V.$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V_{DS}	20	V	
Gate-Source Voltage	V_{GS}	± 8	V	
Continuous Drain Current	I_D	5	A	
Pulsed Drain Current	I_{DM}	20	A	
Maximum Power Dissipation	P_D	$T_A = 25^\circ C$	2.0	W
		$T_A = 70^\circ C$	1.6	W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	78	$^\circ C/W$	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	40	$^\circ C/W$	
Junction temperature and Storage temperature	T_J, T_{stg}	-55 to +150	$^\circ C$	